

## 2018年度発表

主発表者	所属	発表先	タイトル	課題番号
Atsushi Iizuka	東北大学	Materials Transactions <b>Vol.59 No.5</b> (2018), 843-849	Scorodite Synthesis in As(V)-Containing Fe(II) Solution in the Presence of Hematite as a Fe(III) Source	1611103PT
Toshihiro Okajima	青山学院大学	Materials Express Research, <b>5</b> (2018), 046412	Geometric structure of Sn dopants in sputtered TiO <sub>2</sub> film revealed by x-ray absorption spectroscopy and first-principles DFT calculations	1504023F
Hiroshi Uemachi	関西学院大学	Electrochimica Acta, <b>281</b> (2018), 99-108	X-ray absorption near edge structure analysis of the charge-discharge mechanisms of dithiobiuret polymer used as a high-capacity cathode material for lithium-ion batteries	1011112GT
Kazuya Miura	スズキ株式会社	e-Journal of Surface Science and Nanotechnology, <b>Vol.16</b> (2018), 209-213	DFT Study for Supported Pt Catalysts Focusing on the Chemical Potential	1705030G
Yi Liu	九州大学	Polymer Journal, <b>51</b> (2018),189-198	Smectic Ordered Structure and Water Repellency of a Poly(fluoroalkyl acrylate) with a Carbamate Linker	1612115F 1707063F
Hirotaaka Yamaguchia	産業技術総合研究所	Journal of Applied Crystallography, <b>51</b> (2018), 1372-1377	Stacking faults in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> crystals observed by X-ray topography	1707054G
Satoshi Masuya	佐賀大学大学院	Diamond & Related Materials, <b>90</b> (2018), 40-46	Dislocations in chemical vapor deposition (111) single crystal diamond observed by synchrotron X-ray topography and their relation with etch pits	1605029S 1607059S 1609075S 1610092S 1612119S 1601143S 1702003S 1703011S 1704021S 1706047S 1707079S
Mohamed Egiza	九州大学大学院	Coatings, <b>8</b> (2018), 359	Effects of Air Exposure on Hard and Soft X-ray Photoemission Spectra of Ultrananocrystalline Diamond/Amorphous Carbon Composite Films	1410105S 1508064S 1607062S 1610090S
Hiroto Nishihara	大阪産業技術研究所	Journal of Materials Chemistry A, <b>6</b> (2018), 12523-12531	Enhanced hydrogen chemisorption and spillover on non-metallic nickel subnanoclusters	1508068S
二宮翔	九州大学大学院	鉄と鋼, <b>Vol. 104</b> <b>No.11</b> (2018), 628-633	軟X線吸収分光法によるフェライト鋼中微量固溶炭素の化学状態観察	1601149S 1705026Pi 1707068F

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R. Ohtani	九州大学大学院	Inorganic Chemistry, <b>57</b> (2018), 11588–11596	Positive and negative two-dimensional thermal expansions via relaxation of node distortions	1606042F
R. Ohtani	九州大学大学院	Dalton Transactions, <b>48</b> (2018), 7198–7202	Consecutive oxidative additions of iodine on undulating 2D coordination polymers: formation of I–Pt–I chains and	1606042F
Akihiko Toda	山口大学大学院	Polymer, <b>169</b> (2019), 11–20	Crystallization and melting behaviors of poly(vinylidene fluoride) examined by fast-scan calorimetry: Hoffman–Weeks, Gibbs–Thomson and thermal Gibbs–Thomson plots	1604027A 1702008A
Naoto Nishiyama	山口大学大学院	Catalysis Science & Technology, <b>8</b> (2018), 4726–4733	Factors affecting photocatalytic activity of visible light-responsive titanium dioxide doped with chromium ions	1607058R
A. Kitajou	山口大学	J. Power Sources, <b>419</b> (2019),1–5	Electrochemical properties of titanium fluoride with high rate capability for lithium-ion batteries	1607055R
S.Shikata	関西学院大学	Japanese Journal of Applied Physics, <b>58</b> (2019), 045503	Dislocation analysis of homoepitaxial diamond (001) film by x-ray topography	1703009R 1711120R 1802001A
S.Shikata	関西学院大学	Japanese Journal of Applied Physics, <b>57</b> (2018), 111301	Precise measurements of diamond lattice constant	1610088R
阪東恭子	産業技術総合研究所	Bulletin of the Chemical Society of Japan, <b>91</b> (2018), 1731–1738	Photoluminescent Properties and Local Structure of Tb Doped Fibrous Alumina	1411125F 1511110F 1610133F
Takayoshi Oshima	佐賀大学大学院	Japanese Journal of Applied Physics, <b>57</b> (2018), 080308	Measurements of the band alignment at coherent $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> heterojunctions	1712123F
Naoto Nishiyama	山口大学大学院	Catal. Sci. Technol., <b>8</b> (2018), 4726–4733	Factors affecting photocatalytic activity of visible light-responsive titanium dioxide doped with chromium ions	1607058R
Hiroto Nishihara	大阪市立工業研究所	J. Mater. Chem. A, <b>6</b> (2018), 12523–12531	Enhanced hydrogen chemisorption and spillover on non-metallic nickel subnanoclusters	1508068S
Yogesh Kumar Maurya	九州大学大学院	J. Am. Chem. Soc., <b>140</b> , <b>22</b> (2018), 6883–6892	Ground-State Copper(III) Stabilized by N-Confused/N-Linked Corroles: Synthesis, Characterization, and Redox Reactivity	1802151G
Hiromasa Suo	産業技術総合研究所	Japanese Journal of Applied Physics, <b>57</b> (2018), 065501	Evaluation of the increase in threading dislocation during the initial stage of physical vapor transport growth of 4H–SiC	1702007A
Keitaro Eguchi	名古屋大学大学院	The Journal of Physical Chemistry C, <b>122</b> (2018), 26054–26060	In Situ Real-Time Measurements for Ambipolar Channel Formation Processes in Organic Double-Layer Field-Effect Transistors of CuPc and F16CuPc	1705033F 1707067F
Shinich Shikata	関西学院大学	Jap.J.Appl.Phys., <b>57</b> (2018), 111301	Precise measurements of diamond lattice constant using Bond method	1610088R

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澤田啓二	東北大学多元物質科学研究所	X線分析の進歩, <b>50</b> (2019), 248-260	X線吸収分光を用いた特殊鋼製鋼スラグ中のFeおよびCrの化学状態分析	1712138R 1804018R 1807055R 1809076R
J. R. Stellhorn	熊本大学	AIP Conference Proceedings, <b>2054</b> (2019), 050012-1-7	Anomalous x-ray scattering experiments for disordered materials at the SAGA Light Source	1706046F 1802007A
Noritake Isomura	株式会社豊田中央研究所	Journal of Synchrotron Radiation, <b>26</b> (2019),	Distinguishing nitrogen-containing sites in SiO <sub>2</sub> /4H-SiC(0001) after nitric oxide annealing by X-ray absorption spectroscopy	1706043G 1801149G
Shohei Hayashi	産業技術総合研究所	Japanese Journal of Applied Physics, <b>58</b> (2019), 011005	Structural analysis of interfacial dislocations and expanded single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-i-n diodes	1702007A
Hiromasa Suo	産業技術総合研究所	Japanese Journal of Applied Physics, <b>58</b> (2019), 021001	Observation of multilayer Shockley-type stacking fault formation during process of epitaxial growth on highly nitrogen-doped 4H-SiC substrate	1702007A
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Shohei Hayashi	産業技術総合研究所	Japanese Journal of Applied Physics, <b>58</b> (2019),	Structural analysis of interfacial dislocations and expanded single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-i-n diodes	1702007A 1802006A